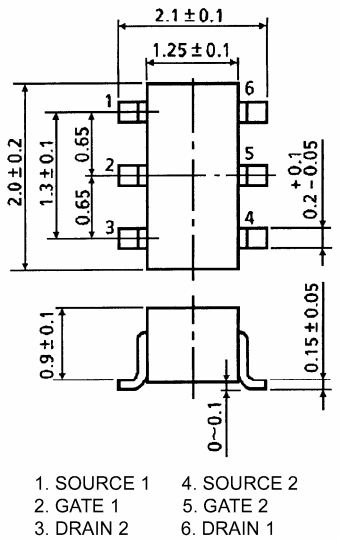
TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (U-MOSIII)

SSM6N48FU

Load Switching Applications

- 2.5-V drive
- N-ch 2-in-1
- Low ON-resistance: $R_{DS(ON)}$ = 3.2 Ω (max) (@V_{GS} = 4.0 V)
  $R_{DS(ON)}$ = 5.4 Ω (max) (@V_{GS} = 2.5 V)

Unit: mm



US6

JEDEC	—
JEITA	SC-88
TOSHIBA	2-2J1C

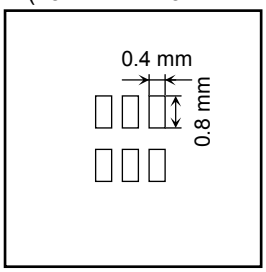
Weight: 6.8 mg (typ.)

Absolute Maximum Ratings (Ta = 25°C)
(Q1, Q2 Common)

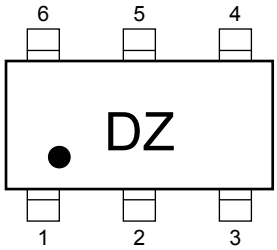
Characteristics		Symbol	Rating	Unit
Drain-Source voltage		V_{DSS}	30	V
Gate-Source voltage		V_{GSS}	±20	V
Drain current	DC	I_D	100	mA
	Pulse	I_{DP}	400	
Power dissipation		P_D (Note 1)	300	mW
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.
Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

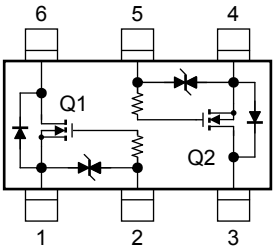
Note 1: Total rating
Mounted on an FR4 board
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 0.32mm^2 × 6)



Marking



Equivalent Circuit (top view)



Start of commercial production
2010-08

Electrical Characteristics (Ta = 25°C) (Q1, Q2 Common)

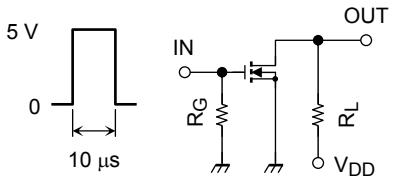
Characteristics		Symbol	Test Condition	Min	Typ.	Max	Unit
Drain-Source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 0.1 mA, V_{GS} = 0 V	30	—	—	V
		$V_{(BR)\ DSX}$	I_D = 0.1 mA, V_{GS} = -10 V (Note 3)	16	—	—	
Drain cut-off current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	—	—	1	μA
Gate leakage current		I_{GSS}	V_{GS} = ±12 V, V_{DS} = 0 V	—	—	±1	μA
Gate threshold voltage		V_{th}	V_{DS} = 3 V, I_D = 0.1 mA	0.8	—	1.5	V
Forward transfer admittance		$\lvert Y_{fs} \rvert$	V_{DS} = 3 V, I_D = 10 mA (Note 2)	33	—	—	mS
Drain-Source ON resistance		$R_{DS\ (ON)}$	I_D = 10 mA, V_{GS} = 4 V (Note 2)	—	2.0	3.2	Ω
			I_D = 10 mA, V_{GS} = 2.5 V (Note 2)	—	3.0	5.4	
Input capacitance		C_{iss}	V_{DS} = 3 V, V_{GS} = 0 V, f = 1 MHz	—	15.1	—	pF
Reverse transfer capacitance		C_{rss}		—	7.8	—	
Output capacitance		C_{oss}		—	12.4	—	
Switching time	Turn-on time	t_{on}	V_{DD} = 5 V, I_D = 10 mA, V_{GS} = 0 to 5 V, R_G = 50 Ω	—	35	—	ns
	Turn-off time	t_{off}		—	180	—	
Drain-source forward voltage		V_{DSF}	I_D = -100 mA, V_{GS} = 0 V (Note 2)	—	-0.83	-1.2	V

Note 2: Pulse test

Note 3: If a reverse bias is applied between gate and source, this device enters V(BR)DSX mode. Note that the drain-source breakdown voltage is lowered in this mode.

Switching Time Test Circuit

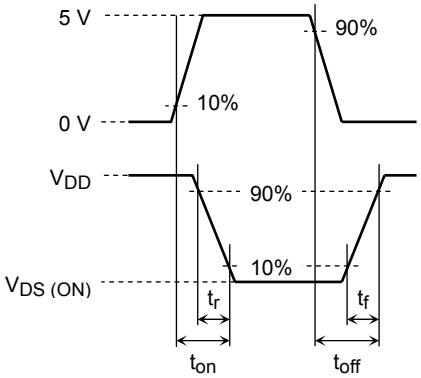
(a) Test circuit



V_{DD} = 5 V
R_G= 50 Ω
Duty ≤ 1%
V_{IN}: t_r, t_f < 5 ns
Common Source
Ta = 25°C

(b) V_{IN}

(c) V_{OUT}



Precaution

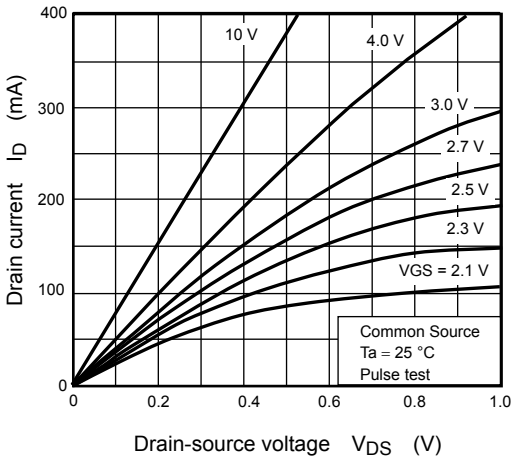
V_{th} can be expressed as voltage between gate and source when low operating current value is I_D = 0.1 mA for this product. For normal switching operation, $V_{GS\ (on)}$ requires higher voltage than V_{th} and $V_{GS\ (off)}$ requires lower voltage than V_{th}. (Relationship can be established as follows: $V_{GS\ (off)} < V_{th} < V_{GS\ (on)}$)
Please take this into consideration for using the device.

Do not use this device under avalanche mode. It may cause the device to break down.

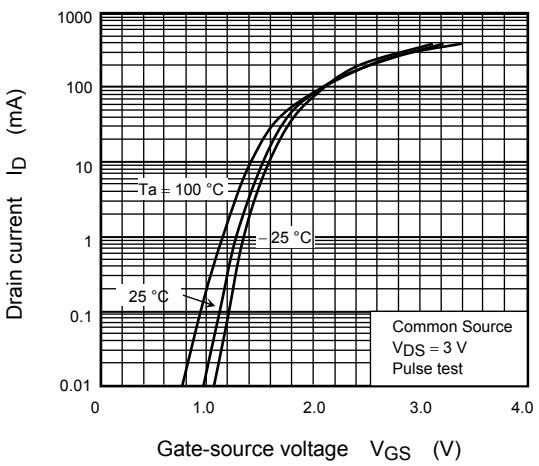
Handling Precaution

When handling individual devices (which are not yet mounting on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

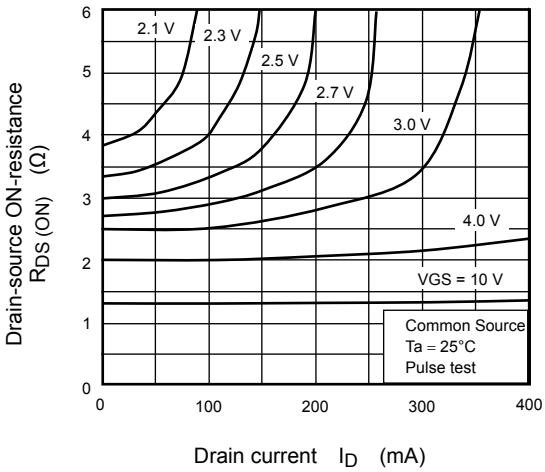
$I_D – V_{DS}$



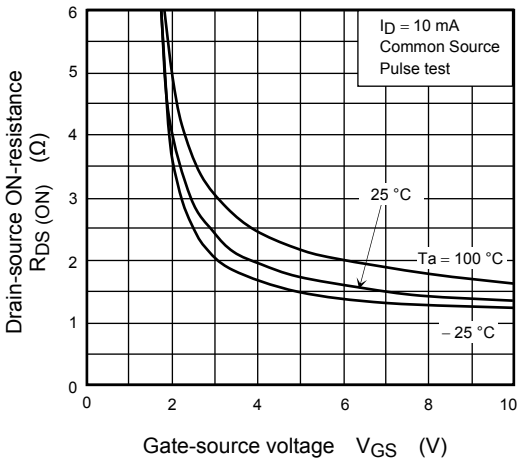
$I_D – V_{GS}$



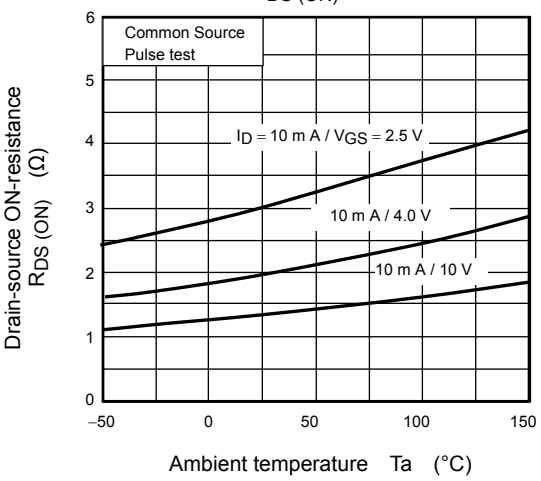
$R_{DS\ (ON)} – I_D$



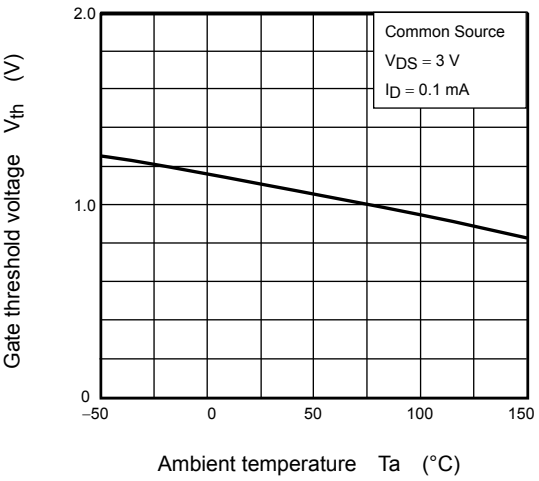
$R_{DS\ (ON)} – V_{GS}$

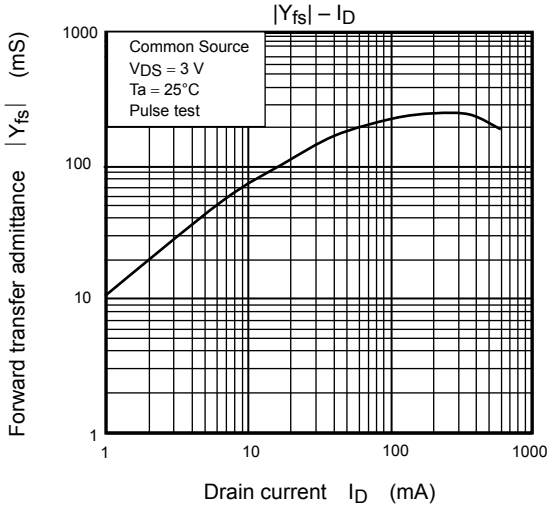


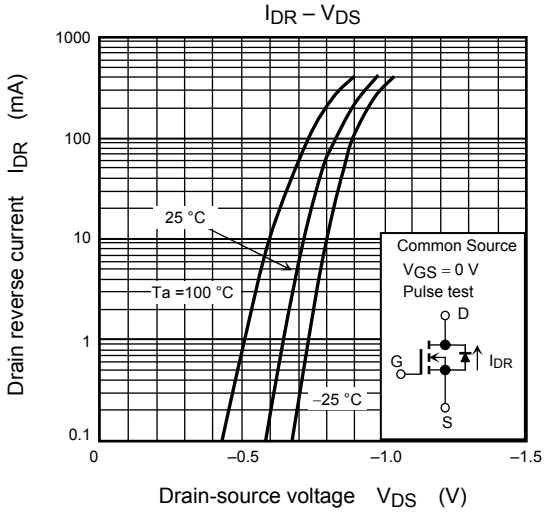
$R_{DS\ (ON)} – Ta$

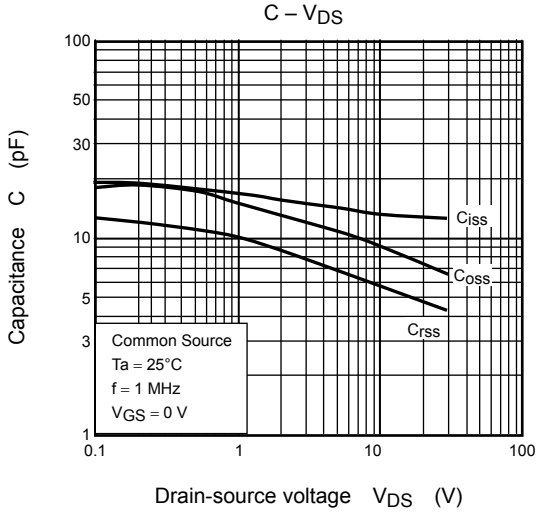


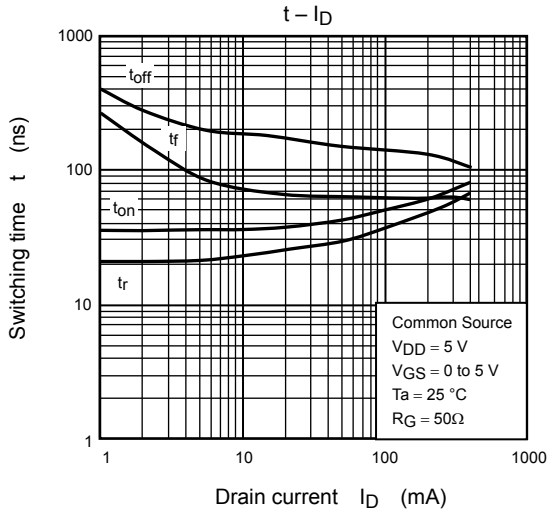
$V_{th} – Ta$

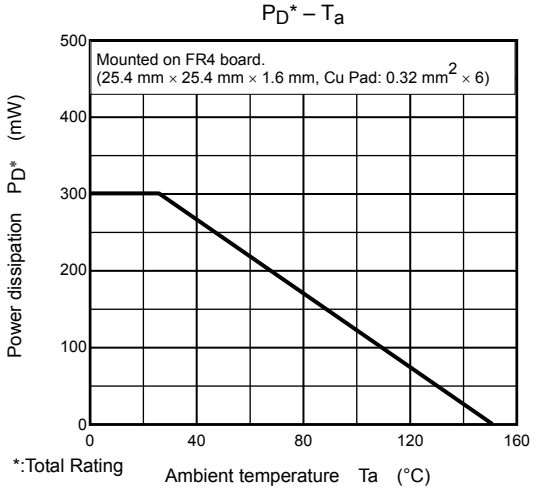



|Yfs| – ID
Common Source
VDS = 3 V
Ta = 25°C
Pulse test
Forward transfer admittance |Yfs| (mS)
Drain current ID (mA)
1000
100
10
1
1
10
100
1000


IDR – VDS
Common Source
VGS = 0 V
Pulse test
25 °C
Ta =100 °C
−25 °C
D
G
S
IDR
Drain reverse current IDR (mA)
Drain-source voltage VDS (V)
1000
100
10
1
0.1
0
−0.5
−1.0
−1.5


C – VDS
Ciss
Coss
Crss
Common Source
Ta = 25°C
f = 1 MHz
VGS = 0 V
Capacitance C (pF)
Drain-source voltage VDS (V)
100
50
30
10
5
3
1
0.1
1
10
100


t – ID
toff
tf
ton
tr
Common Source
VDD = 5 V
VGS = 0 to 5 V
Ta = 25 °C
RG = 50Ω
Switching time t (ns)
Drain current ID (mA)
1000
100
10
1
1
10
100
1000


PD* – Ta
Mounted on FR4 board.
(25.4 mm × 25.4 mm × 1.6 mm, Cu Pad: 0.32 mm2 × 6)
Power dissipation PD* (mW)
Ambient temperature Ta (°C)
*:Total Rating
500
400
300
200
100
0
0
40
80
120
160

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